

SANYO	No.3339	2SC4476
		NPN Triple Diffused Planar Silicon Transistor High-Voltage Amp, High-Voltage Switching Applications

Applications

- High voltage amp
- High voltage switching
- Dynamic focus

Features

- High breakdown voltage ($V_{CEO \text{ min}} = 1800V$)
- Small c_{ob} ($c_{ob \text{ typ}} = 1.8pF$)
- Wide ASO
- High reliability (Adoption of HVP process)

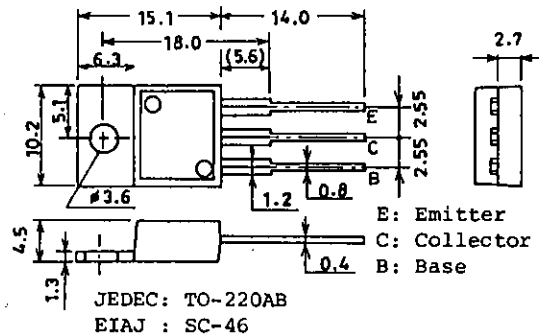
Absolute Maximum Ratings at $T_a = 25^\circ C$

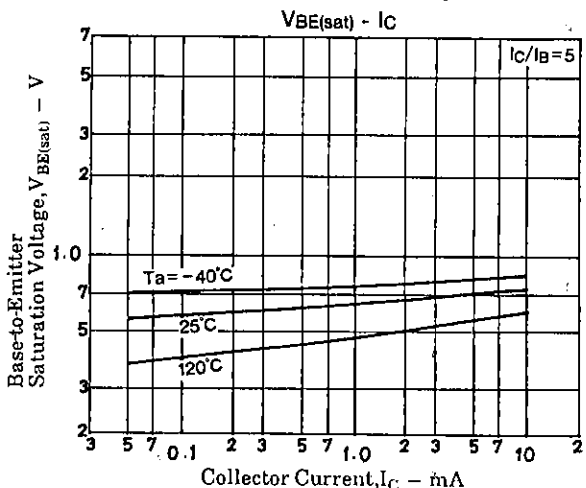
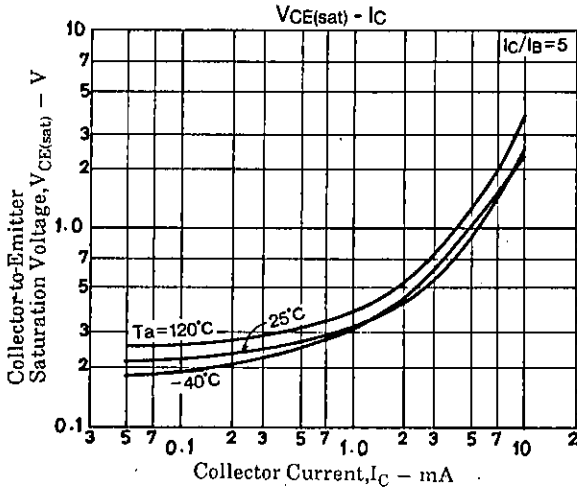
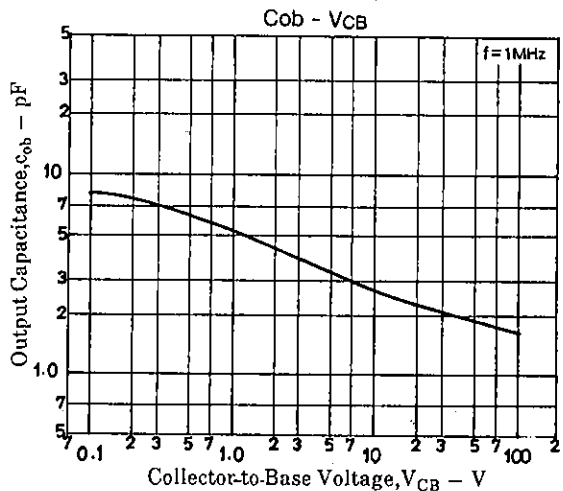
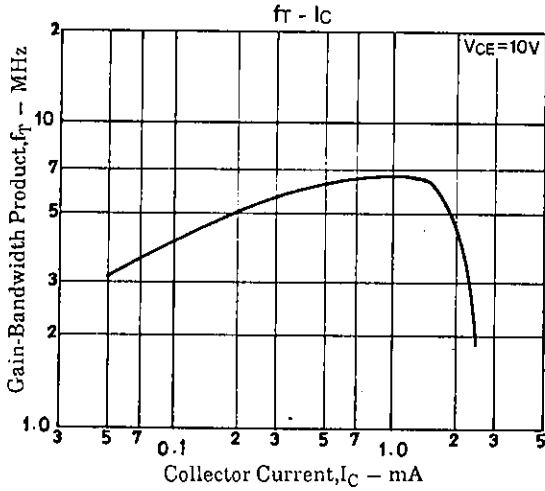
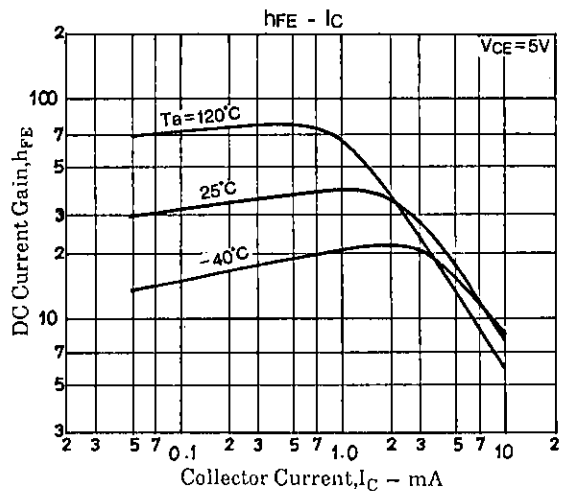
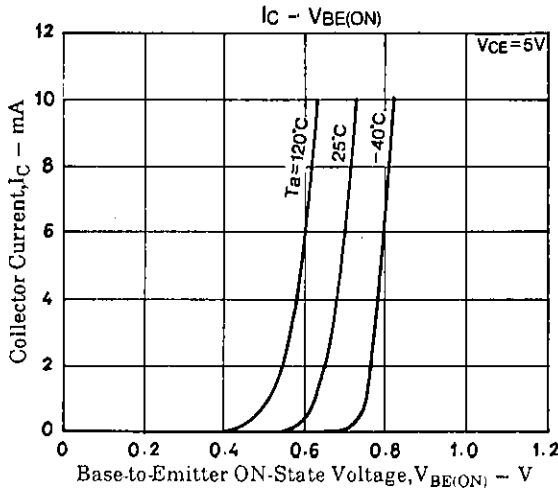
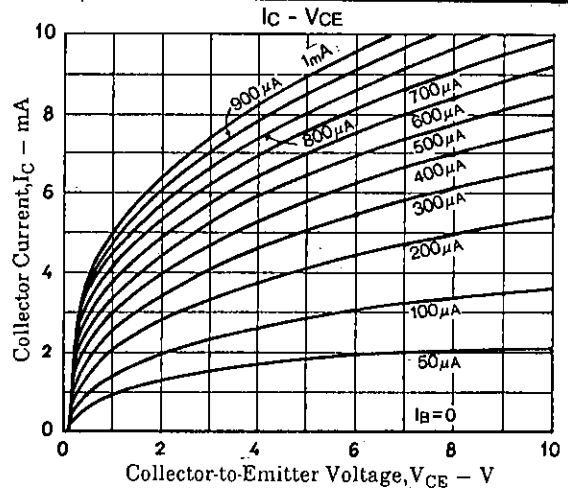
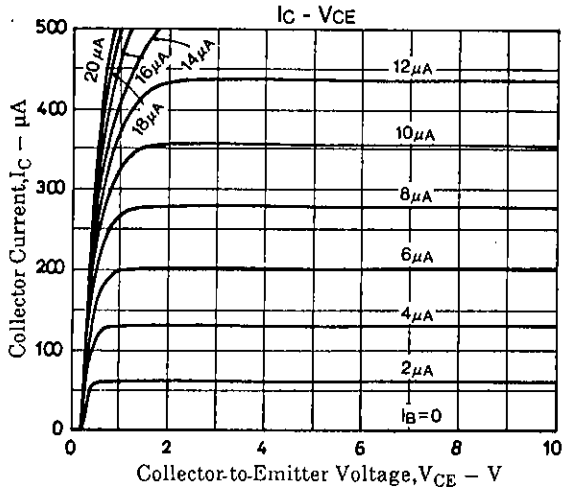
			unit
Collector-to-Base Voltage	V_{CBO}	2000	V
Collector-to-Emitter Voltage	V_{CEO}	1800	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	10	mA
Peak Collector Current	i_{cp}	30	mA
Collector Dissipation	P_C	1.75	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

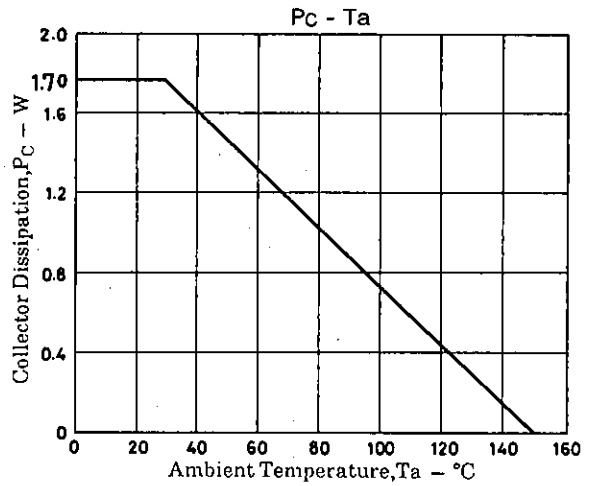
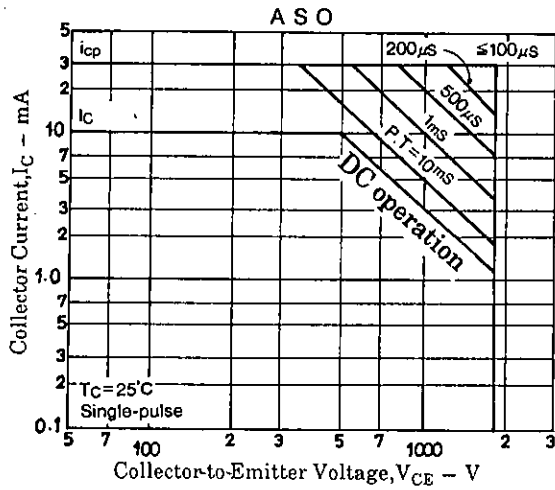
Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1800V, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 300\mu A$	10		60	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 300\mu A$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 600\mu A, I_B = 120\mu A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 600\mu A, I_B = 120\mu A$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	2000			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu A, R_{BE} = \infty$	1800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V
Output Capacitance	c_{ob}	$V_{CB} = 100V, f = 1MHz$		1.8		pF

Package Dimensions 2010B
(unit: mm)







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